

Application Serial No. 10/712,921
Reply to office action of May 17, 2005

PATENT
Docket: CU-3455

Amendments To The Specification

Please replace the paragraph on the specification page 14, lines 3 to 8 with the following amended paragraph:

Referring to FIG. 3d, the resulting structure formed by the above processes is heated to a temperature higher than 800 °C for thermal diffusion of the ion-implanted impurities. At this time, ~~depletion~~ the thermal diffusion occurs below the dotted line in the portion indicated by the oblique lines. This implies that the depletion at the gate sidewalls is reduced.